# **BUJD105AD**

# NPN power transistor with integrated diode

Rev. 02 — 29 July 2010

Product data sheet

# 1. Product profile

### 1.1 General description

High voltage, high speed, planar passivated NPN power switching transistor with integrated anti-parallel E-C diode in a SOT428 (DPAK) surface-mountable plastic package.

#### 1.2 Features and benefits

- Fast switching
- High voltage capability

Very low switching and conduction losses

## 1.3 Applications

- DC-to-DC converters
- Electronic lighting ballasts
- Inverters
- Motor control systems

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>C</sub>	collector current	see Figure 1; see Figure 2; DC	-	-	8	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> ≤ 25 °C; see <u>Figure 3</u>	-	-	80	W
$V_{CESM}$	collector-emitter peak voltage	$V_{BE} = 0 V$	-	-	700	V
Static chara	acteristics					
h <sub>FE</sub>	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 4 \text{ A}; T_{mb} = 25 \text{ °C};$ see <u>Figure 9</u> ; see <u>Figure 10</u>	8	12.5	-	



# 2. Pinning information

Table 2. Pinning information

	_			
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		_
2	С	collector[1]	mb	c L
3	E	emitter	1 3	B E sym131
			SOT428 (DPAK)	

<sup>[1]</sup> It is not possible to make a connection to pin 2 of the SOT428 (DPAK) package.

# 3. Ordering information

Table 3. Ordering information

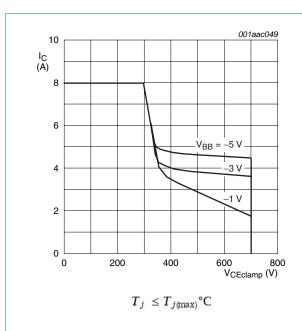
Type number	Package		
	Name	Description	Version
BUJD105AD	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CESM}$	collector-emitter peak voltage	$V_{BE} = 0 V$	-	700	V
$V_{CBO}$	collector-base voltage	I <sub>E</sub> = 0 A	-	700	V
V <sub>CEO</sub>	collector-emitter voltage	I <sub>B</sub> = 0 A	-	400	V
I <sub>C</sub>	collector current	DC; see Figure 1; see Figure 2	-	8	Α
I <sub>CM</sub>	peak collector current	see Figure 1; see Figure 2	-	16	Α
I <sub>B</sub>	base current	DC	-	4	Α
I <sub>BM</sub>	peak base current		-	8	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> ≤ 25 °C; see <u>Figure 3</u>	-	80	W
T <sub>stg</sub>	storage temperature		-65	150	°C
Tj	junction temperature		-	150	°C



$$\begin{split} V_{\mathit{CL(CE)}} &\leq 1000 \; V; V_{\mathit{CC}} = 150 \; V; V_{\mathit{BB}} = \, -5 \; V; \\ L_{\mathit{B}} &= 1 \, \mu H; L_{\mathit{C}} = 200 \, \mu H \end{split} \label{eq:clce}$$

Fig 1. Reverse bias safe operating area

Fig 2. Test circuit for reverse bias safe operating area

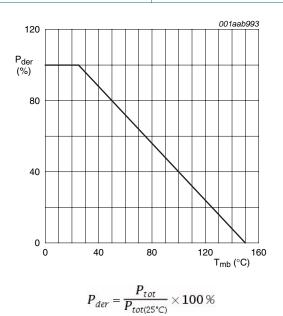
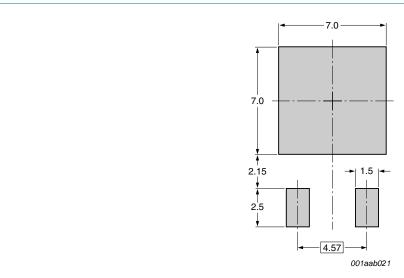


Fig 3. Normalized total power dissipation as a function of mounting base temperature

### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <u>Figure 5</u>	-	-	1.56	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	printed-circuit-board mounted; minimum footprint; see Figure 4	-	75	-	K/W



all dimensions are in mm

Fig 4. Minimum footprint SOT428

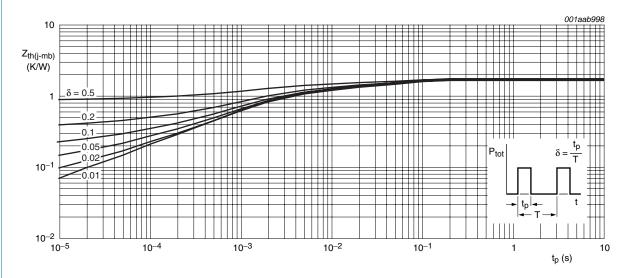


Fig 5. Transient thermal impedance from junction to mounting base as a function of pulse width

# 6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static cha	aracteristics						
I <sub>CES</sub>	collector-emitter cut-off	$V_{BE} = 0 \text{ V}; V_{CE} = 700 \text{ V}; T_j = 25 ^{\circ}\text{C}$	<u>[1]</u>	-	-	0.2	mΑ
	current	V <sub>BE</sub> = 0 V; V <sub>CE</sub> = 700 V; T <sub>j</sub> = 125 °C	<u>[1]</u>	-	-	0.5	mA
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = 700 \text{ V}; I_E = 0 \text{ A}$	<u>[1]</u>	-	-	0.2	mΑ
I <sub>CEO</sub>	collector-emitter cut-off current	$V_{CE} = 400 \text{ V}; I_{B} = 0 \text{ A}$	[1]	-	-	0.1	mA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 9 \text{ V}; I_{C} = 0 \text{ A}$		-	-	10	mΑ
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = 4 \text{ A}$ ; $I_B = 0.8 \text{ A}$ ; see <u>Figure 6</u> ; see <u>Figure 7</u>		-	0.35	1	V
$V_{BEsat}$	base-emitter saturation voltage	$I_C = 4 \text{ A}$ ; $I_B = 0.8 \text{ A}$ ; see <u>Figure 8</u>		-	1	1.5	V
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 4 A; T <sub>j</sub> = 25 °C		-	1.07	1.5	V
h <sub>FE</sub>	DC current gain	$I_C = 4 \text{ A}$ ; $V_{CE} = 5 \text{ V}$ ; $T_{mb} = 25 \text{ °C}$ ; see <u>Figure 9</u> ; see <u>Figure 10</u>		8	12.5	-	
		$I_C = 1 \text{ mA}; V_{CE} = 5 \text{ V}; T_{mb} = 25 \text{ °C}$		10	17	34	
		$I_C = 500 \text{ mA}; V_{CE} = 5 \text{ V}; T_{mb} = 25 \text{ °C}$		13	22	36	
Dynamic	characteristics						
t <sub>on</sub>	turn-on time	$I_C = 5 A$ ; $I_{Bon} = 1 A$ ; $I_{Boff} = -1 A$ ;		-	0.65	1	μs
t <sub>s</sub>	storage time	$R_L$ = 75 Ω; $T_j$ = 25 °C; resistive load; see <u>Figure 11</u> ; see <u>Figure 12</u>		- 1.8	2.5	μs	
		$I_C$ = 5 A; $I_{Bon}$ = 1 A; $V_{BB}$ = -5 V; $L_B$ = 1 $\mu$ H; $T_j$ = 25 °C; inductive load; see Figure 13; see Figure 14		-	1.2	1.7	μs
		$I_C$ = 5 A; $I_{Bon}$ = 1 A; $V_{BB}$ = -5 V; $L_B$ = 1 $\mu$ H; $T_j$ = 100 °C; inductive load; see <u>Figure 13</u> ; see <u>Figure 14</u>		-	1.4	1.9	μs
t <sub>f</sub>	fall time	$I_C$ = 5 A; $I_{Bon}$ = 1 A; $V_{BB}$ = -5 V; $L_B$ = 1 $\mu$ H; $T_{mb}$ = 25 °C; inductive load; see <u>Figure 13</u> ; see <u>Figure 14</u>		-	0.02	0.05	μs
		$I_C$ = 5 A; $I_{Bon}$ = 1 A; $V_{BB}$ = -5 V; $L_B$ = 1 $\mu$ H; $T_{mb}$ = 100 °C; inductive load; see <u>Figure 13</u> ; see <u>Figure 14</u>		-	0.025	0.1	μs
		$I_C$ = 5 A; $I_{Bon}$ = 1 A; $I_{Boff}$ = -1 A; $R_L$ = 75 $\Omega$ ; $T_j$ = 25 °C; resistive load; see Figure 11; see Figure 12		-	0.3	0.5	μs

<sup>[1]</sup> Measured with half-sine wave voltage (curve tracer).

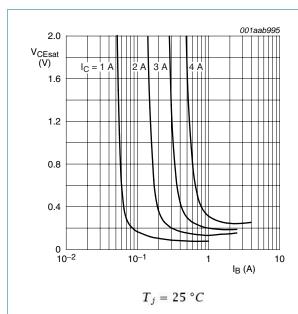


Fig 6. Collector-emitter saturation voltage as a function of base current; typical values

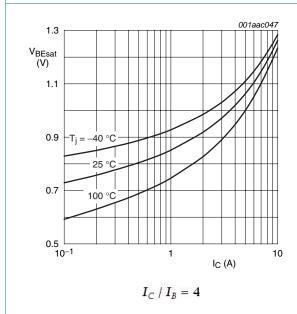


Fig 8. Base-emitter saturation voltage as a function of collector current; typical values

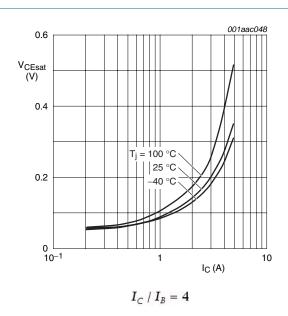


Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values

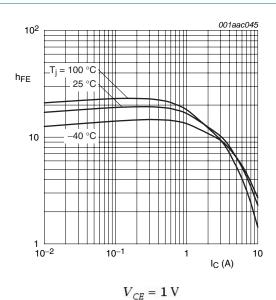


Fig 9. DC current gain as a function of collector current; typical values

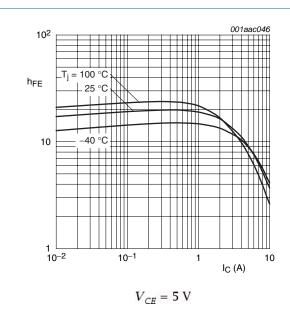
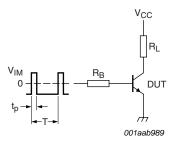


Fig 10. DC current gain as a function of collector current; typical values



$$V_{IM}=-6$$
 to  $+8$   $V$ ;  $V_{CC}=250$   $V$ ;  $t_p=20$   $\mu s$ ;  $\pmb{\delta}=\frac{t_p}{T}=0.01$   $R_B$  and  $R_L$  calculated from  $I_{Con}$  and  $I_{Bon}$  requirements.

Fig 11. Test circuit for resistive load switching

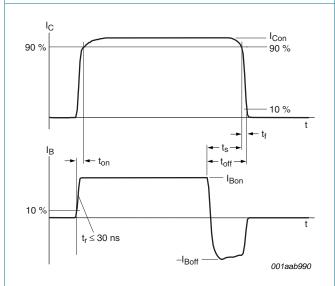
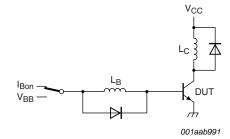
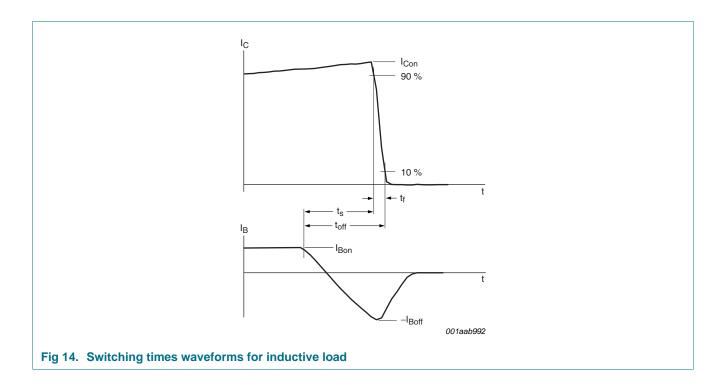


Fig 12. Switching times waveforms for resistive load



$$V_{CC} = 300 \ V; V_{BB} = -5 \ V; L_C = 200 \ \mu H; L_B = 1 \ \mu H$$

Fig 13. Test circuit for inductive load switching



# 7. Package outline

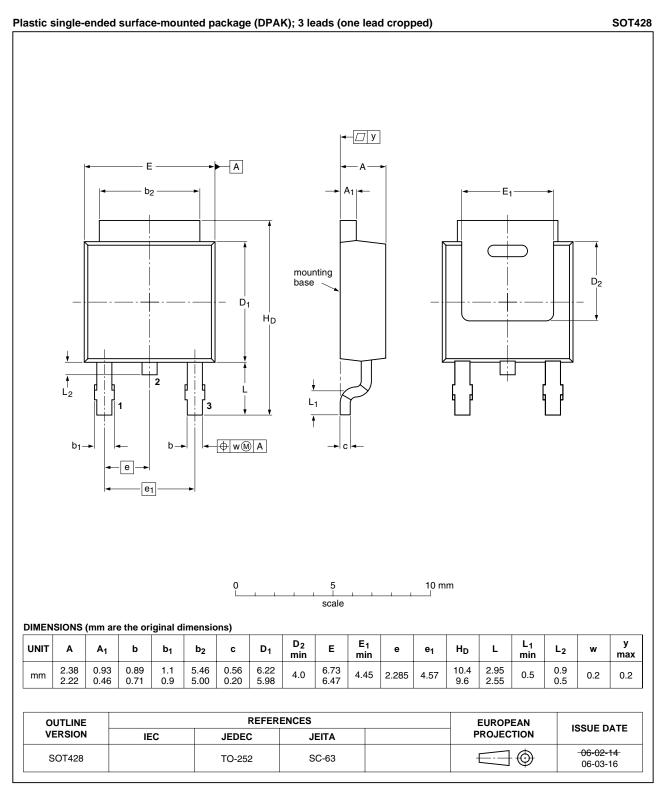


Fig 15. Package outline SOT428 (DPAK)



# 8. Revision history

### Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUJD105AD v.2	20100729	Product data sheet	-	BUJD105AD v.1
Modifications:	<ul> <li>Various chang</li> </ul>	ges to content.		
BUJD105AD v.1	20090508	Product data sheet	-	-

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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- [2] The term 'short data sheet' is explained in section "Definitions"
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# **BUJD105AD**

### NPN power transistor with integrated diode

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